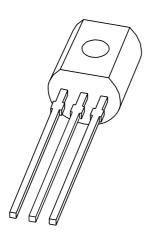
DISCRETE SEMICONDUCTORS

DATA SHEET



PSS9014CNPN general purpose transistor

Product specification Supersedes data of 2002 Mar 15 2002 Sep 20





NPN general purpose transistor

PSS9014C

FEATURES

- High power dissipation: 500 mW
- · Low collector capacitance
- Low collector-emitter saturation voltage
- · High current capability.

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

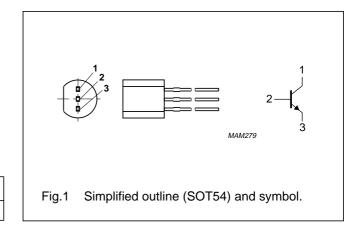
NPN low V_{CEsat} transistor in a SOT54 (TO-92) plastic package.

MARKING

TYPE NUMBER	MARKING CODE
PSS9014C	S9014C

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	50	V
V _{CEO}	collector-emitter voltage	open base	_	45	V
V_{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		_	100	mA
I _{CM}	peak collector current		_	200	mA
I _{BM}	peak base current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	500	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	in free air; note 1	250	K/W
_	ambient			

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 30 V; I _E = 0	_	_	15	nA
		V _{CB} = 30 V; I _E = 0; T _{amb} = 150 °C	_	-	5	μΑ
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0	_	_	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	_	_	100	nA
h _{FE}	DC current gain	I _C = 1 mA; V _{CE} = 5 V	200	300	600	
		I _C = 2 mA; V _{CE} = 5 V	200	300	450	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}; \text{ note 1}$	_	200	300	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = 100 \text{ mA}$; $I_B = 0.5 \text{ mA}$; note 1	_	815	850	mV
V_{BEon}	base-emitter turn-on voltage	$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	580	650	700	mV
f⊤	transition frequency	I _C = 50 mA; V _{CE} = 10 V; f = 100 MHz	100	220	_	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0; f = 1 \text{ MHz}$	_	1.6	1.75	pF
F	noise figure	$V_{CE} = 5 \text{ V; } I_{C} = 0.2 \text{ mA;}$ $R_{S} = 2 \text{ k}\Omega; f = 1 \text{ kHz; } B = 200 \text{ Hz}$	_	_	10	dB

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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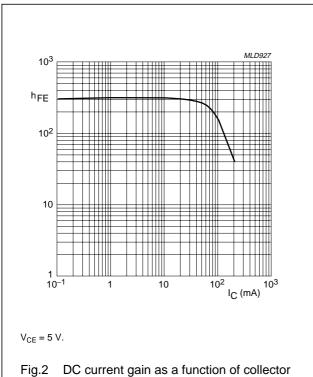


Fig.2 DC current gain as a function of collecto current; typical values.

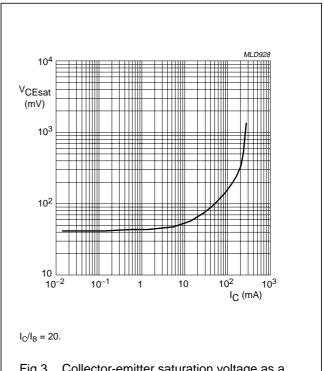
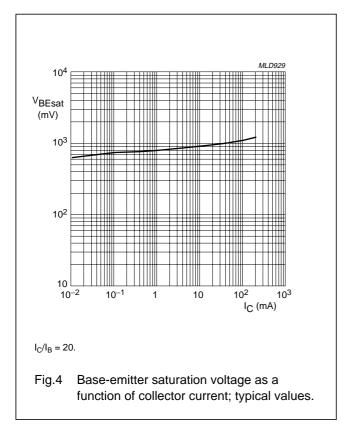
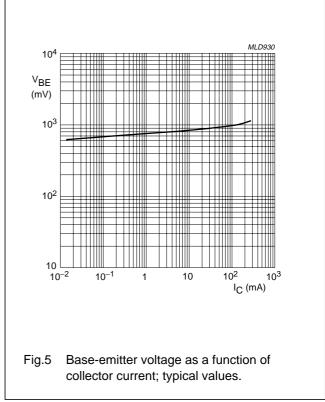


Fig.3 Collector-emitter saturation voltage as a function of collector current; typical values.





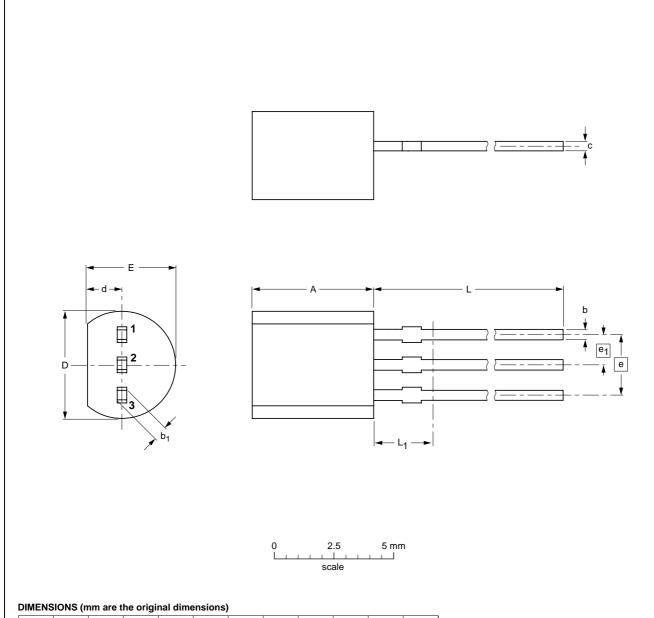
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE	REFERENCES					ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE I		
SOT54		TO-92	SC-43			97-02-28	

NPN general purpose transistor

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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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